

PN930

NPN General Purpose Amplifier

• This device is designed for low noise, high gain, general purpose applications at collector currents from 1µA to 50mA.



1. Emitter 2. Base 3. Collector

Absolute Maximum Ratings* $T_A=25$ °C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	45	V
V_{CBO}	Collector-Base Voltage	45	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	100	mA
T _{J.} T _{STG}	Operating and Storage Junction Temperature Range	- 55 ~ 150	°C

^{*} These ratings are limiting values above which the serviceability of any semiconductor device may be impaird.

- These ratings are based on a maximum junction temperature of 150 degrees C.
 These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations

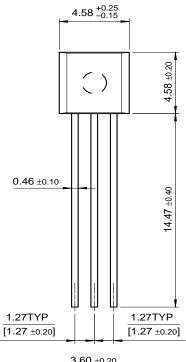
Electrical Characteristics T_A=25°C unless otherwise noted

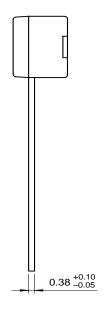
Symbol	Parameter	Test Condition	Min.	Max.	Units
Off Chara	cteristics	•	•	•	
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage *	I _C = 10mA, I _B = 0	45		V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_C = 10\mu A, I_E = 0$	45		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 10nA, I _C = 0	5.0		V
I _{CEO}	Collector Cutoff Current	V _{CE} = 5.0V		2.0	nA
I _{CBO}	Collector Cutoff Current	V _{CB} = 45V, I _E = 0		10	nA
I _{CES}	Collector Cutoff Current	$V_{CB} = 45V, I_{E} = 0$		10	nA
		$V_{CB} = 45V$, $I_{E} = 0$, $T_{A} = 170^{\circ}C$		10	μΑ
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 5.0V, I_{C} = 0$		10	nA
On Charac	cteristics				
h _{FE}	DC Current Gain	$V_{CE} = 5.0V, I_{C} = 10\mu A$	10	300	
		$V_{CE} = 5.0V, I_{C} = 10\mu A, T_{A} = -55^{\circ}C$	20		
		$V_{CE} = 5.0V, I_{C} = 500\mu A$	150		
		$V_{CE} = 5.0V, I_{C} = 10mA$		600	
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 10 \text{mA}, I_B = 0.5 \text{mA}$		1.0	V
V _{BE} (sat)	Base-Emitter Saturation Voltage	$I_C = 10mA, I_B = 0.5mA$	0.6	1.0	V
Small Sigi	nal Characteristics				
C _{ob}	Output Capacitance	V _{CB} = 5.0V, f = 1.0MHz		8.0	pF
h _{fe}	Small Signal Current Gain	$I_C = 500\mu A$, $V_{CE} = 5.0V$, $f = 20MHz$	1.5		
		$I_C = 1.0 \text{mA}, V_{CE} = 5.0 \text{V}, f = 1.0 \text{KHz}$	150	600	
h _{ib}	Input Impedance	$I_C = 1.0 \text{mA}, V_{CE} = 5.0 \text{V}, f = 1.0 \text{KHz}$	25	32	Ω
h _{rb}	Voltage Feedback Ratio			600	x10 ⁻⁶
h _{ob}	Output Admittance			1.0	μmho
NF	Noise Figure	V_{CE} = 5.0V, I_{C} = 10μA R_{G} = 10KΩ, B_{W} = 15.7KHz		3.0	dB

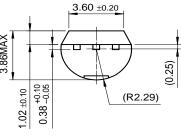
Thermal Characteristics T _A =25°C unless otherwise noted			
Symbol	Parameter	Max.	Units
P_{D}	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case 83.3		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient 200		°C/W

Package Dimensions

TO-92







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